

1. General description

NPN low V_{CEsat} transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\rm I}_{\rm C}$ and ${\rm I}_{\rm CM}$
- + High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current			-	-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	1.5	А
R _{CEsat}	collector-emitter saturation resistance	$\begin{array}{l} I_{C} = 1 \text{ A}; I_{B} = 0.1 \text{ A}; pulsed; t_{p} \leq \ 300 \ \mus; \\ \delta \leq \ 0.02; T_{amb} = 25 \ ^{\circ}C \end{array}$		-	170	235	mΩ

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5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	В	base					
2	E	emitter		С			
3	С	collector	4	в			
4	С	collector		E			
			Transparent top view DFN1010D-3 (SOT1215)	sym123			

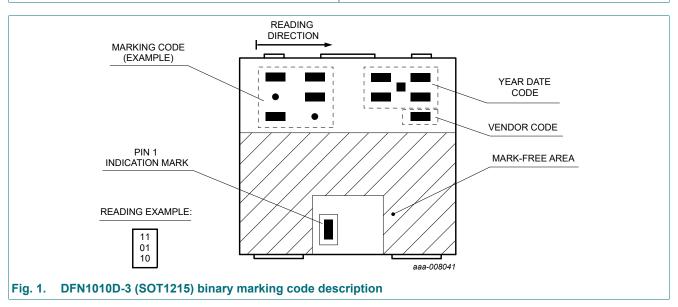
6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4160QA-Q		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 3 terminals; 0.75 mm pitch; 1.1 mm x 1 mm x 0.37 mm body	<u>SOT1215</u>		

7. Marking

Table 4. Marking codes Type number Marking code PBSS4160QA-Q 11 00 10



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1.5	А
I _B	base current			-	0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

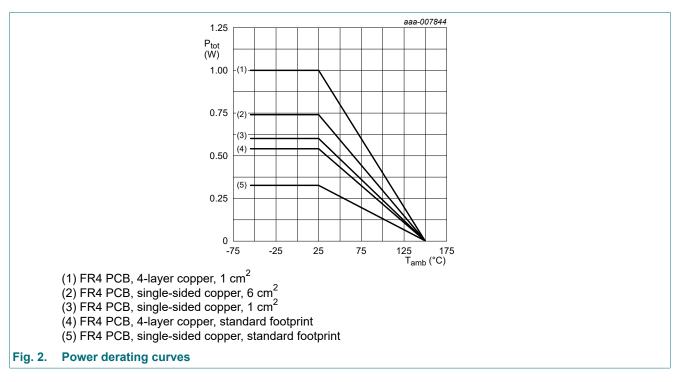
[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².



9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from		[1]	-	-	385	K/W
	junction to ambient		[2]	-	-	209	K/W
			[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm²₂.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

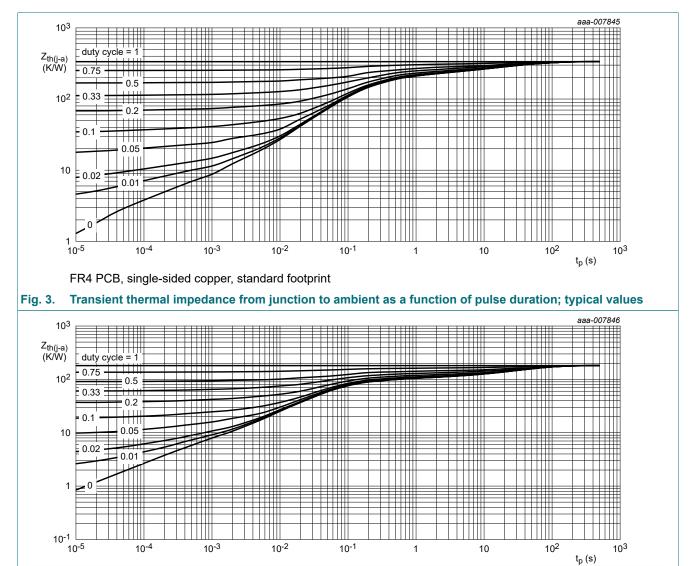
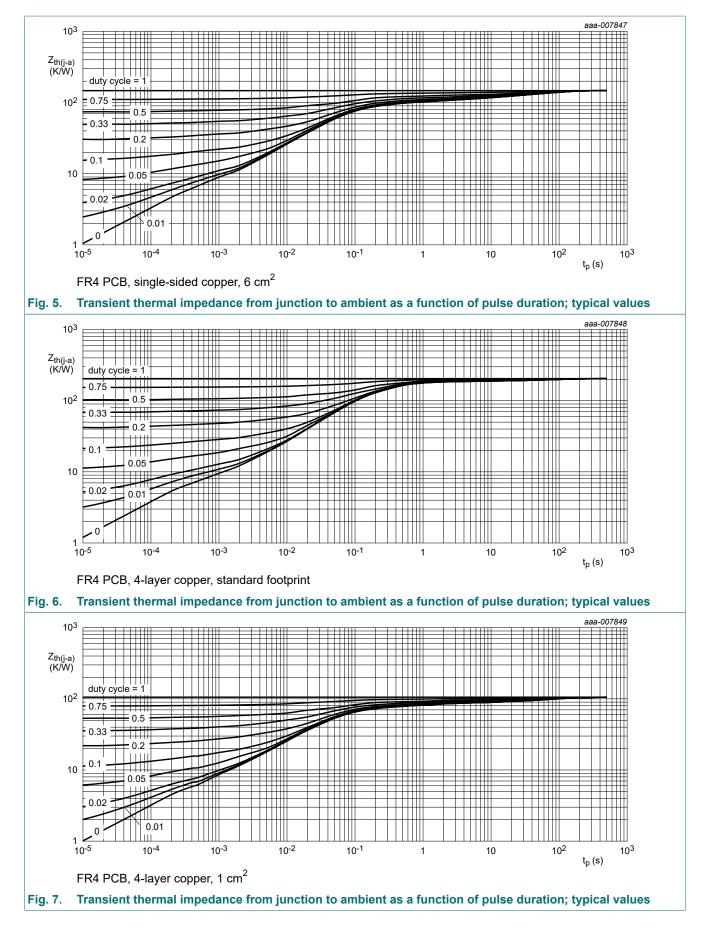


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

FR4 PCB, single-sided copper, 1 cm²

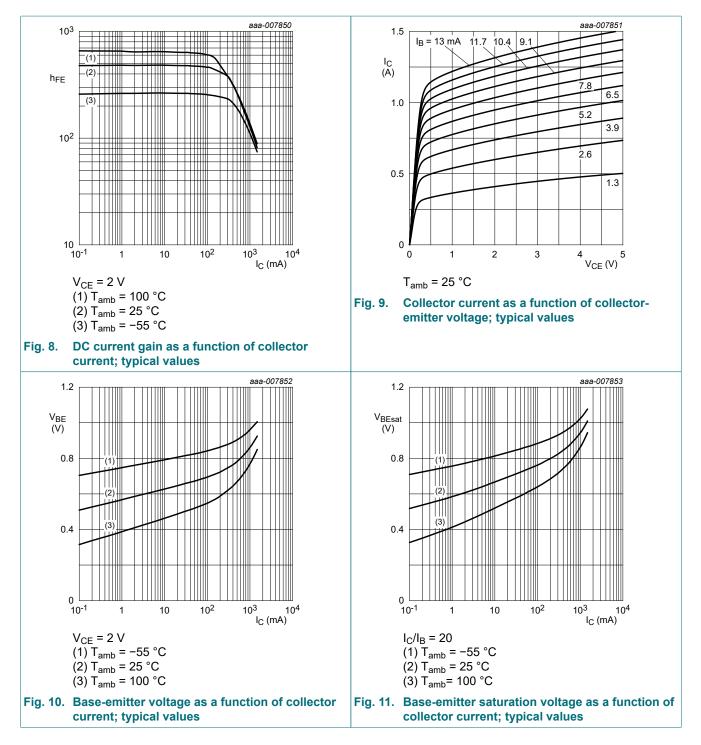
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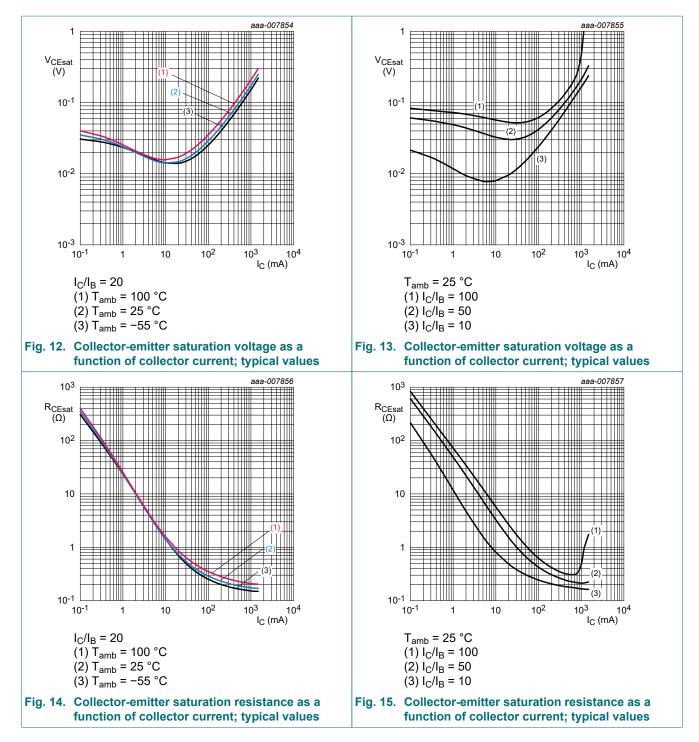
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	230	400	-	
		V _{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	150	240	-	
		V_{CE} = 2 V; I _C = 1 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	85	130	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	125	mV
		I _C = 1 A; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	180	245	mV
		I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	170	235	mV
R _{CEsat}	collector-emitter saturation resistance	$\begin{array}{l} I_{C} = 1 \; A; \; I_{B} = 0.1 \; A; \; pulsed; \; t_{p} \leq \; 300 \; \mu s; \\ \delta \leq \; 0.02; \; T_{amb} = 25 \; ^{\circ} \mathrm{C} \end{array}$	-	170	235	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.89	1	V
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.94	1.05	V
		I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.98	1.1	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 0.5 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.78	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = -25 mA; T _{amb} = 25 °C	-	85	-	ns
t _{on}	turn-on time		-	100	-	ns
t _s	storage time		-	545	-	ns
t _f	fall time		-	125	-	ns
t _{off}	turn-off time		-	670	-	ns
f _T	transition frequency	V _{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	120	180	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.7	6	pF

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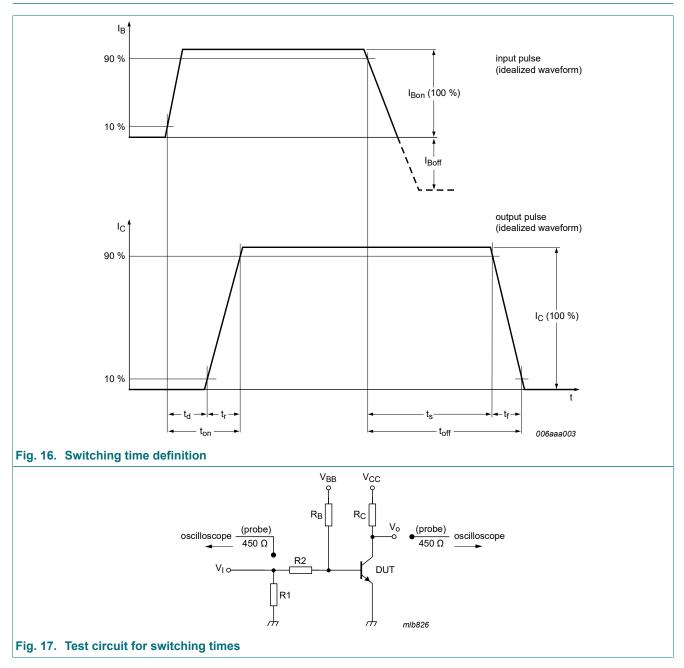


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11. Test information

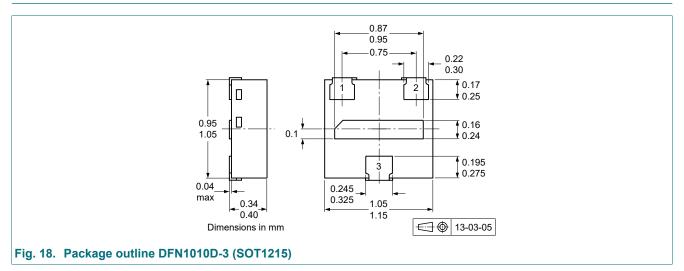


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

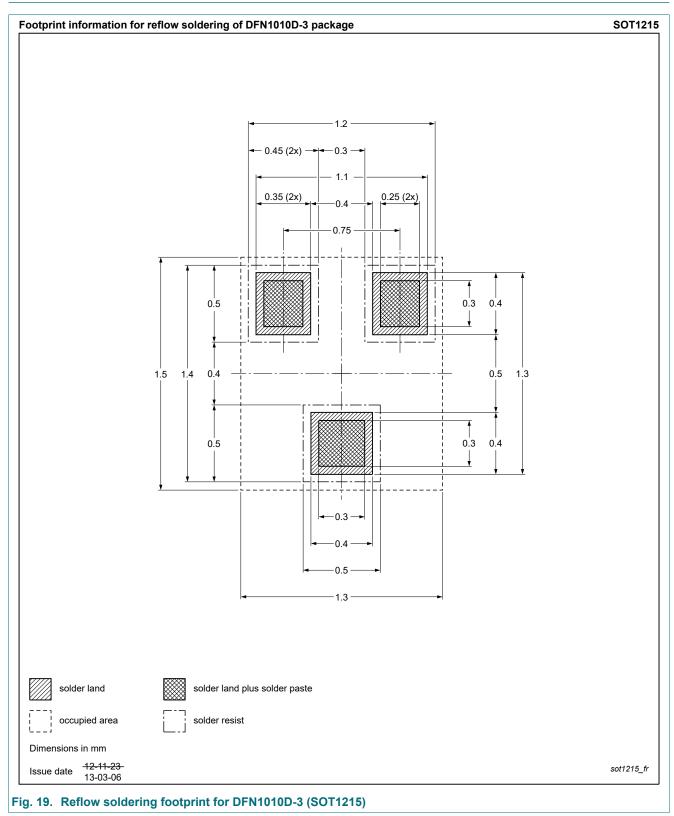
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4160QA-Q v.1	20230309	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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